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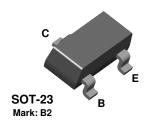
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# **BSV52**



# **NPN Switching Transistor**

This device is designed for high speed saturated switching at collector currents of 10 mA to 100 mA. Sourced from Process 21.

### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	12	V
V <sub>CES</sub>	Collector-Base Voltage	20	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stq</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BSV52	
P <sub>D</sub>	Total Device Dissipation	225	mW
	Derate above 25°C	1.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	556	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	12		V
V <sub>(BR)CES</sub>	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	20		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100  \mu A, I_C = 0$	5.0		V
Ісво	Collector-Cutoff Current	$V_{CB} = 10 \text{ V}, I_{E} = 0$		100	nA
		$V_{CB} = 10 \text{ V}, I_E = 0, T_A = 125^{\circ}\text{C}$		5.0	μA
ON CHAF	RACTERISTICS				
h <sub>FE</sub>	DC Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	25		
		$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40	120	
		$I_{\rm C} = 50 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$	25		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$		0.3 0.25	V V
		$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.25	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 3.0 \text{ mA}$	0.7	0.85	V
BE(Sat)	Zaso Zimitor Saturation Voltage		0.7		
		$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		1.2	V
		I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5.0 mA		1.2	V
SMALLS	IGNAL CHARACTERISTICS	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5.0 mA		1.2	V
	IGNAL CHARACTERISTICS		400	1.2	1
	IGNAL CHARACTERISTICS  Transition Frequency	$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V},$	400	1.2	MHz
f <sub>T</sub>	<u> </u>		400	4.0	1
f <sub>T</sub>	Transition Frequency	$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	400		MHz
SMALL S  fT  Ccb  Ceb	Transition Frequency  Collector-Base Capacitance	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz $I_E = 0, V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	400	4.0	MHz pF
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub>	Transition Frequency  Collector-Base Capacitance  Emitter-Base Capacitance	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz $I_E = 0, V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	400	4.0	MHz pF
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub> SWITCHII	Transition Frequency  Collector-Base Capacitance  Emitter-Base Capacitance  NG CHARACTERISTICS	$\begin{split} I_{C} &= 10 \text{ mA, } V_{CE} = 10 \text{ V,} \\ f &= 100 \text{ MHz} \\ I_{E} &= 0, V_{CB} = 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ I_{C} &= 0, V_{EB} = 1.0 \text{ V, } f = 1.0 \text{ MHz} \end{split}$	400	4.0	MHz pF pF
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub> SWITCHII	Transition Frequency  Collector-Base Capacitance  Emitter-Base Capacitance  NG CHARACTERISTICS  Storage Time	$\begin{split} I_C &= 10 \text{ mA}, V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ I_E &= 0, V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz} \\ I_C &= 0, V_{EB} = 1.0 \text{ V}, f = 1.0 \text{ MHz} \\ \end{split}$	400	4.0 4.5	MHz pF pF
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub> SWITCHII	Transition Frequency  Collector-Base Capacitance  Emitter-Base Capacitance  NG CHARACTERISTICS	$\begin{split} I_{C} &= 10 \text{ mA, } V_{CE} = 10 \text{ V,} \\ f &= 100 \text{ MHz} \\ I_{E} &= 0, V_{CB} = 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ I_{C} &= 0, V_{EB} = 1.0 \text{ V, } f = 1.0 \text{ MHz} \end{split}$	400	4.0	MHz pF pF

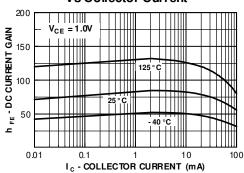
# **Spice Model**

 $NPN \; (Is=44.14f \;\; Xti=3 \;\; Eg=1.11 \;\; Vaf=100 \;\; Bf=78.32 \;\; Ne=1.389 \;\; Ise=91.95f \;\; Ikf=.3498 \;\; Xtb=1.5 \;\; Br=12.69m \;\; Nc=2 \;\; Isc=0 \;\; Ikr=0 \;\; Rc=.6 \;\; Cjc=2.83p \;\; Mjc=86.19m \;\; Vjc=.75 \;\; Fc=.5 \;\; Cje=4.5p \;\; Mje=.2418 \;\; Vje=.75 \;\; Tr=1.073u \;\; Tf=227.6p \;\; Itf=.3 \;\; Vtf=4 \;\; Xtf=4 \;\; Rb=10)$ 

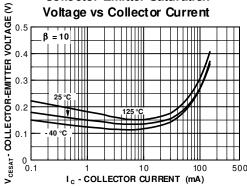
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### **Typical Characteristics**

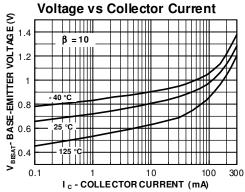




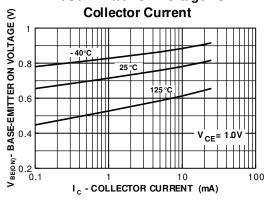
### **Collector-Emitter Saturation** Voltage vs Collector Current



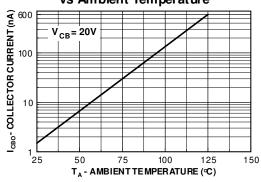
**Base-Emitter Saturation** 



Base-Emitter ON Voltage vs

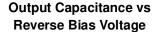


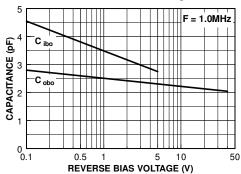
**Collector-Cut off Current** vs Ambient Temperature



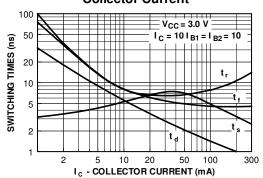
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#### Typical Characteristics (continued)

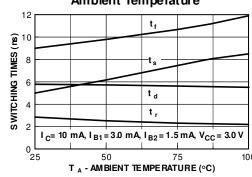




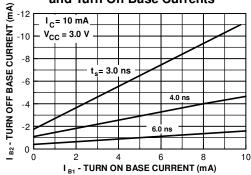
#### Switching Times vs Collector Current



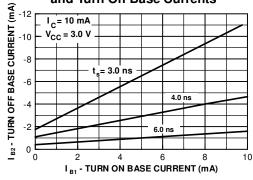
#### Switching Times vs Ambient Temperature



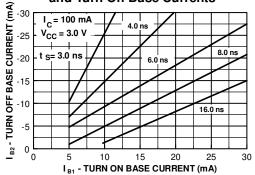
Storage Time vs Turn On and Turn Off Base Currents



Storage Time vs Turn On and Turn Off Base Currents

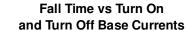


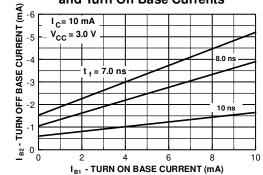
Storage Time vs Turn On and Turn Off Base Currents



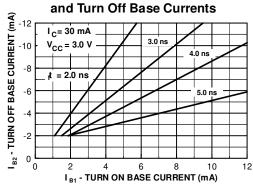
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#### Typical Characteristics (continued)

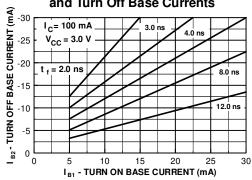




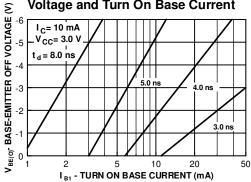
# Fall Time vs Turn On



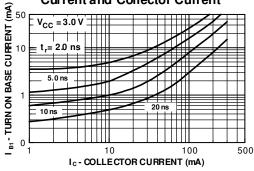
Fall Time vs Turn On and Turn Off Base Currents



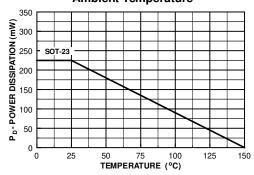
Delay Time vs Base-Emitter OFF Voltage and Turn On Base Current



Rise Time vs. Turn On Base Current and Collector Current



Power Dissipation vs Ambient Temperature



(continued)

### **Test Circuits**

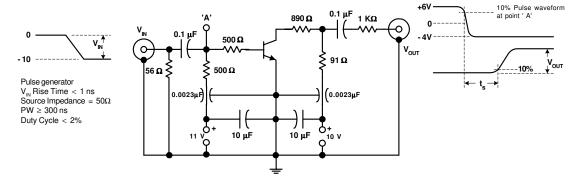


FIGURE 1: Charge Storage Time Measurement Circuit

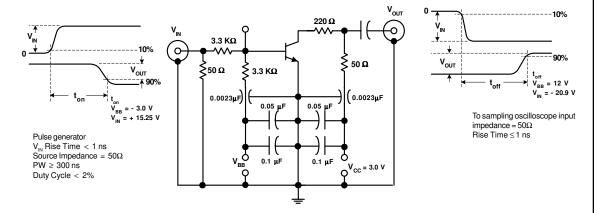


FIGURE 2:  $\mathbf{t}_{\text{ON}}, \mathbf{t}_{\text{OFF}}$  Measurement Circuit

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